

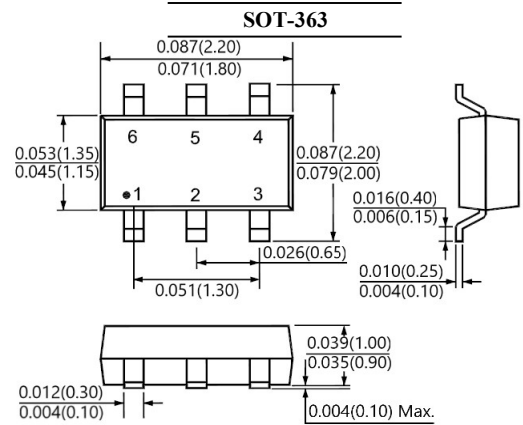
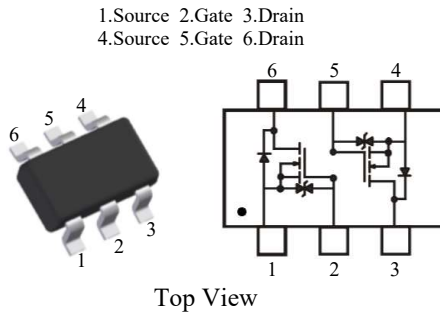


BSS138KDW H

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- ESD protected up to 2kV
- Suffix "H" indicates Halogen-free parts, ex. BSS138KDW H



Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Maximum Drain Current	I_D	360	mA
Peak Drain Current	I_{DM}	1.2	A
Power Dissipation	P_D	236	mW
Thermal Resistance, Junction-to-ambient ⁽¹⁾	$R_{\theta JA}$	530	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Note:

1. $R_{\theta JA}$ is the sum of the junction to case to case ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltag	$I_D = 250 \mu\text{A}$	BV_{DSS}	50	-	V
Drain-Source Leakage Current	$V_{DS} = 50 \text{ V}$	I_{DSS}	-	1	μA
Gate-Body Leakage Current	$V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	± 10	μA
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	0.8	1.5	V
Drain-Source On-State Resistance	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$	$R_{DS(on)}$	-	1.6	Ω
	$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$		-	2.5	
	$V_{GS} = 2.5 \text{ V}, I_D = 100 \text{ mA}$		-	4.5	
Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V},$ $f = 1 \text{ MHz}$	C_{iss}	-	50	pF
Output Capacitance		C_{oss}	-	20	
Reverse Transfer Capacitance		C_{rss}	-	5	
Turn-On Delay Time	$V_{GS} = 10 \text{ V}, V_{DD} = 25 \text{ V}, R_G = 6 \Omega,$ $I_D = 500 \text{ mA}$	$t_{d(on)}$	-	5	nS
Turn-On Rise Time		t_r	-	38	
Turn-Off Delay Time		$t_{d(off)}$	-	12	
Turn-Off Fall Time		t_f	-	50	
Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 500 \text{ mA}$	V_{SD}	-	1.5	V



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RATINGS AND CHARACTERISTIC CURVES

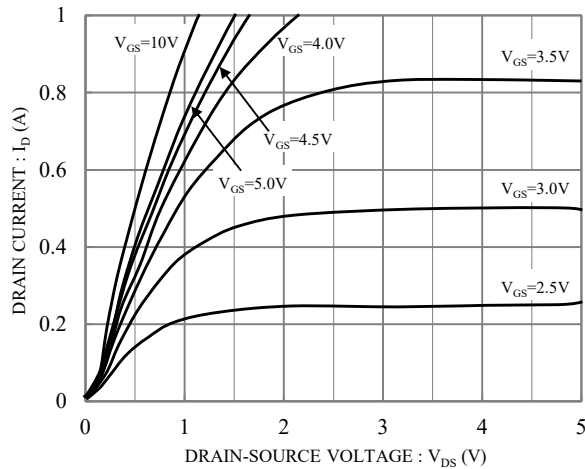


Fig.1 Typical output characteristics

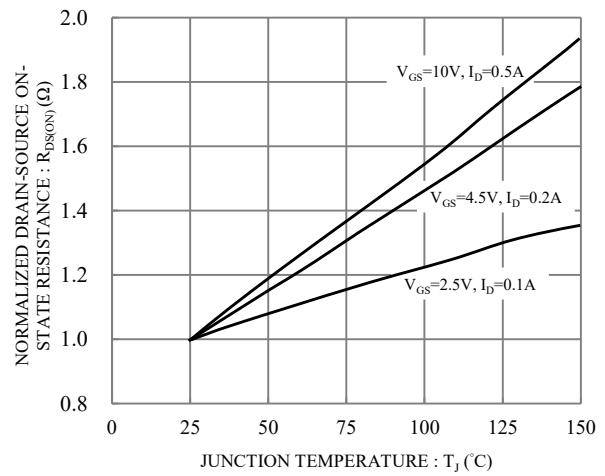


Fig.2 Drain-source on-state resistance vs. Junction temperature

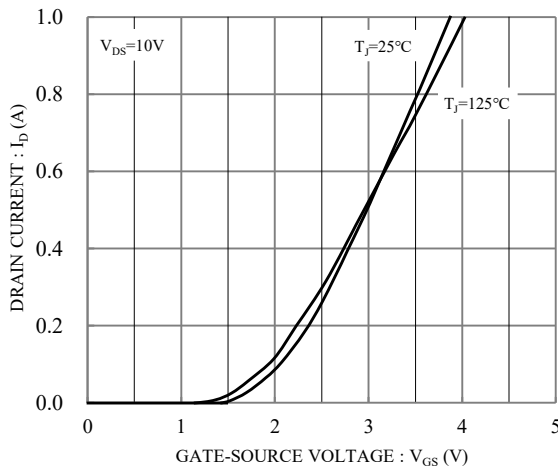


Fig.3 Drain current vs. Gate-source voltage

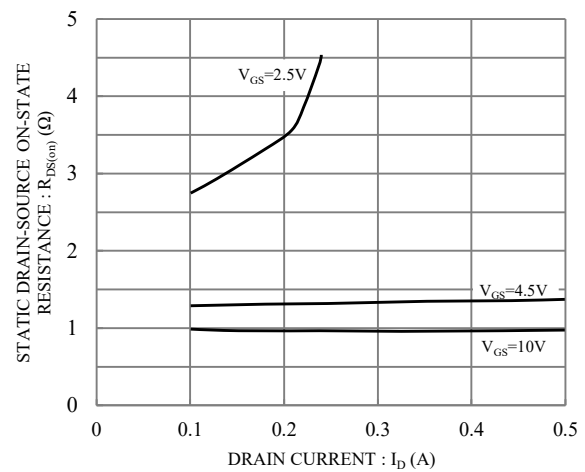


Fig.4 Static drain-source on-state resistance vs. Drain current

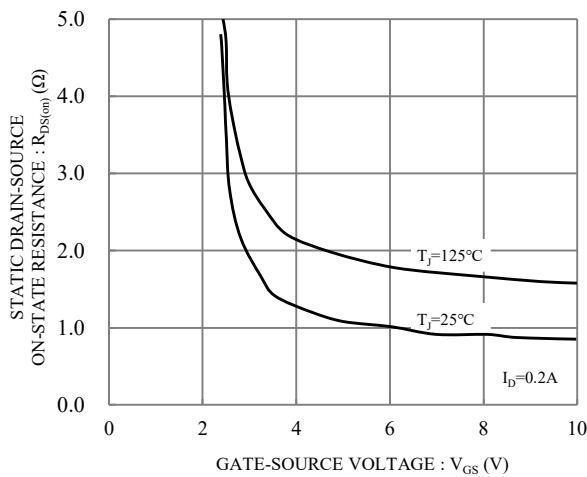


Fig.5 Static drain-source on-state resistance vs. Gate-source voltage

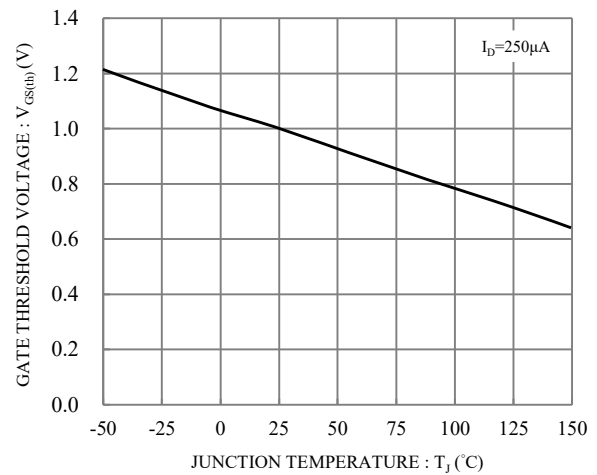


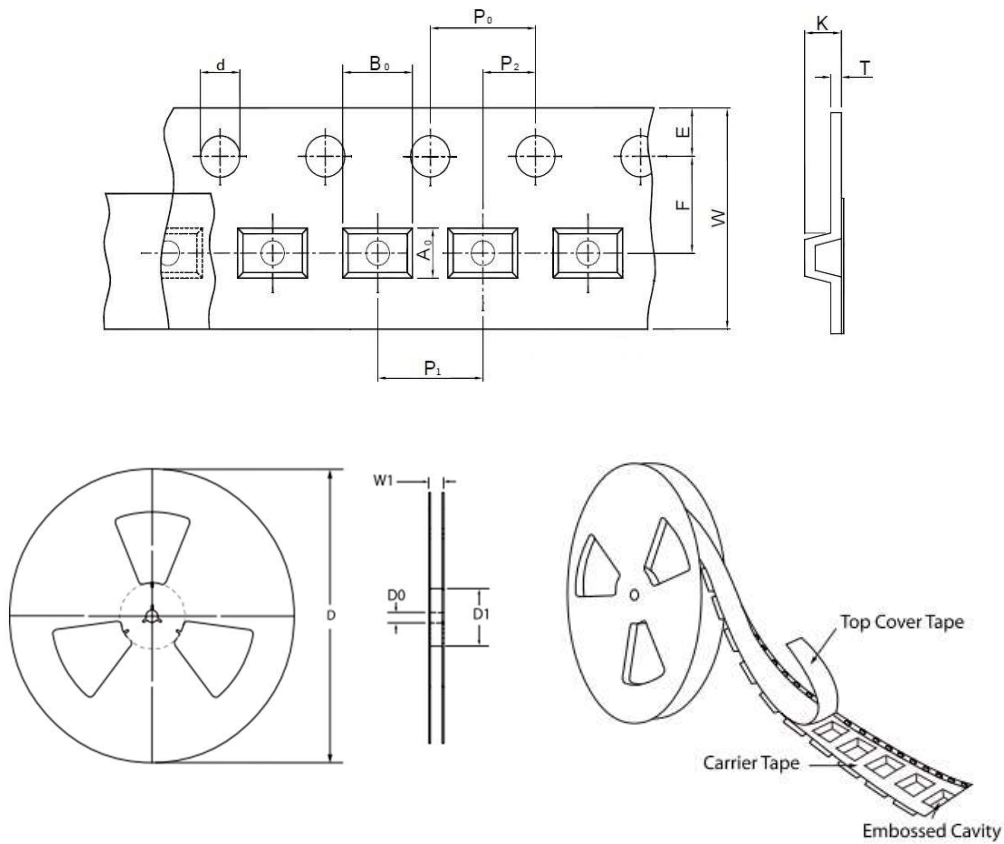
Fig.2 Gate threshold voltage vs. Junction temperature



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TAPE & REEL SPECIFICATION



Item	Symbol	SOT-363
Carrier width	A_0	2.30 ± 0.10
Carrier length	B_0	2.30 ± 0.10
Carrier depth	K_0	1.20 ± 0.10
Sprocket hole	d	1.50 ± 0.10
Reel outside diameter	D	178.00 ± 2.00
Feed hole width	D_0	13.00 ± 0.50
Reel inner diameter	D_1	MIN. 50.00
Sprocket hole position	E	1.75 ± 0.10
Punch hole position	F	3.50 ± 0.10
Sprocket hole pitch	P_0	4.00 ± 0.10
Punch hole pitch	P_1	4.00 ± 0.10
Embossment center	P_2	2.00 ± 0.10
Overall tape thickness	T	0.60 ± 0.10
Tape width	W	8.00 ± 0.30
Reel width	W_1	MAX. 10.00

ORDER INFORMATION

Package	Reel Size	Quantity
SOT-363	7"	3,000

MARKING CODE

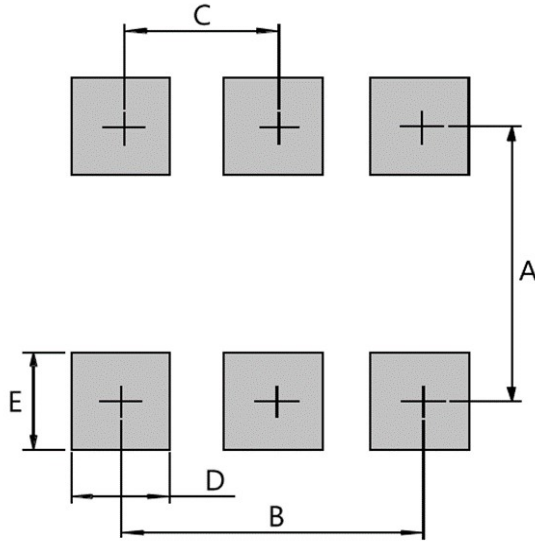
Part Number	Marking Code
BSS138KDW H	NL



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SUGGESTED SOLDER PAD LAYOUT



Unit : mm

PACKAGE	A	B	C	D	E
SOT-363	1.90	1.30	0.65	0.42	0.60